

FDFMA2N028Z

Integrated N-Channel PowerTrench® MOSFET and Schottky Diode

20V, 3.7A, 68mΩ

Features

MOSFET

- Max $r_{DS(on)}$ = 68mΩ at $V_{GS} = 4.5V$, $I_D = 3.7A$
- Max $r_{DS(on)}$ = 86mΩ at $V_{GS} = 2.5V$, $I_D = 3.3A$

Schottky

- $V_F < 0.37V$ @ 500mA
- Low profile - 0.8 mm maximum - in the new package MicroFET 2x2 mm
- RoHS Compliant



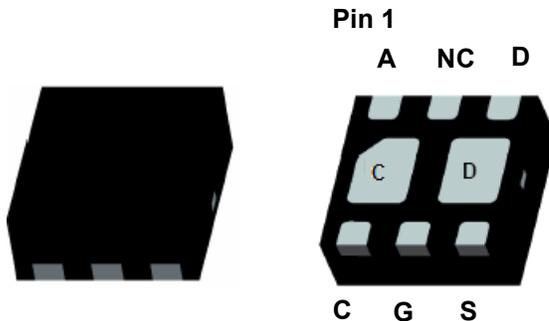
General Description

This device is designed specifically as a single package solution for a boost topology in cellular handset and other ultra-portable applications. It features a MOSFET with low on-state resistance, and an independently connected schottky diode with low forward voltage.

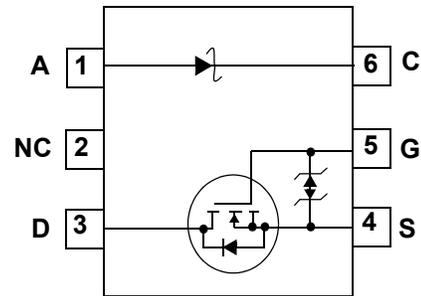
The MicroFET 2x2 package offers exceptional thermal performance for its physical size and is well suited to switching and linear mode applications.

Application

- DC - DC Conversion



MicroFET 2X2



MOSFET Maximum Ratings $T_J = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	20	V
V_{GS}	Gate to Source Voltage	± 12	V
I_D	Drain Current -Continuous (Note 1a)	3.7	A
	-Pulsed	6	
P_D	Power Dissipation (Note 1a)	1.4	W
	Power Dissipation (Note 1b)	0.7	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$
V_{RR}	Schottky Repetitive Peak Reverse Voltage	20	V
I_O	Schottky Average Forward Current	2	A

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	86	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	173	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1c)	86	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1d)	140	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
.N28	FDFMA2N028Z	MicroFET 2X2	7"	8mm	3000 units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C		15		$\text{mV}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 16\text{V}, V_{GS} = 0\text{V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 12\text{V}, V_{DS} = 0\text{V}$			± 10	μA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	0.6	1.0	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C		-4		$\text{mV}/^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 4.5\text{V}, I_D = 3.7\text{A}$		37	68	m Ω
		$V_{GS} = 2.5\text{V}, I_D = 3.3\text{A}$		50	86	
		$V_{GS} = 4.5\text{V}, I_D = 3.7\text{A}, T_J = 125^\circ\text{C}$		53	90	
g_{FS}	Forward Trans conductance	$V_{DS} = 10\text{V}, I_D = 3.7\text{A}$		16		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$		340	455	pF
C_{oss}	Output Capacitance			80	110	pF
C_{rss}	Reverse Transfer Capacitance			60	90	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 10\text{V}, I_D = 1\text{A}$ $V_{GS} = 4.5\text{V}, R_{GEN} = 6\Omega$		8	16	ns
t_r	Rise Time			8	16	ns
$t_{d(off)}$	Turn-Off Delay Time			14	26	ns
t_f	Fall Time			3	6	ns
$Q_{g(TOT)}$	Total Gate Charge		$V_{DS} = 10\text{V}, I_D = 3.7\text{A}$		4	6
Q_{gs}	Gate to Source Gate Charge	$V_{GS} = 4.5\text{V}$		0.7		nC
Q_{gd}	Gate to Drain "Miller" Charge			1.1		nC

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain-Source Diode Forward Current				1.1	A
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 1.1\text{A}$ (Note 2)		0.7	1.2	V
t_{rr}	Reverse Recovery Time	$I_F = 3.7\text{A}, di/dt = 100\text{A}/\mu\text{s}$		11		ns
Q_{rr}	Reverse Recovery Charge			2		nC

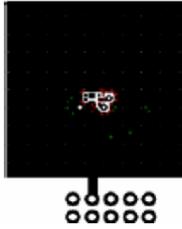
Schottky Diode Characteristics

V_R	Reverse Voltage	$I_R = 1\text{mA}$	$T_J = 25^\circ\text{C}$	20			V
I_R	Reverse Leakage	$V_R = 20\text{V}$	$T_J = 25^\circ\text{C}$		30	300	μA
			$T_J = 125^\circ\text{C}$		10	45	mA
V_F	Forward Voltage	$I_F = 500\text{mA}$	$T_J = 25^\circ\text{C}$		0.32	0.37	V
			$T_J = 125^\circ\text{C}$		0.21	0.26	
		$I_F = 1\text{A}$	$T_J = 25^\circ\text{C}$		0.37	0.435	
			$T_J = 125^\circ\text{C}$		0.28	0.33	

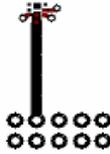
Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Notes:

- 1: $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz. copper pad on a 1.5×1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.
- (a) MOSFET $R_{\theta JA} = 86^\circ\text{C/W}$ when mounted on a 1in^2 pad of 2 oz copper, $1.5'' \times 1.5'' \times 0.062''$ thick PCB.
 - (b) MOSFET $R_{\theta JA} = 173^\circ\text{C/W}$ when mounted on a minimum pad of 2 oz copper.
 - (c) Schottky $R_{\theta JA} = 86^\circ\text{C/W}$ when mounted on a 1in^2 pad of 2 oz copper, $1.5'' \times 1.5'' \times 0.062''$ thick PCB.
 - (d) Schottky $R_{\theta JA} = 140^\circ\text{C/W}$ when mounted on a minimum pad of 2 oz copper.



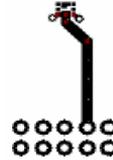
a) 86°C/W when mounted on a 1in^2 pad of 2 oz copper.



b) 173°C/W when mounted on a minimum pad of 2 oz copper.



c) 86°C/W when mounted on a 1in^2 pad of 2 oz copper.



d) 140°C/W when mounted on a minimum pad of 2 oz copper.

- 2: Pulse Test: Pulse Width $< 300\mu\text{s}$, Duty cycle $< 2.0\%$.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

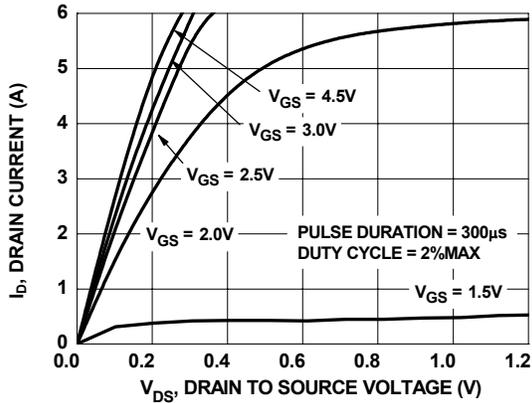


Figure 1. On-Region Characteristics

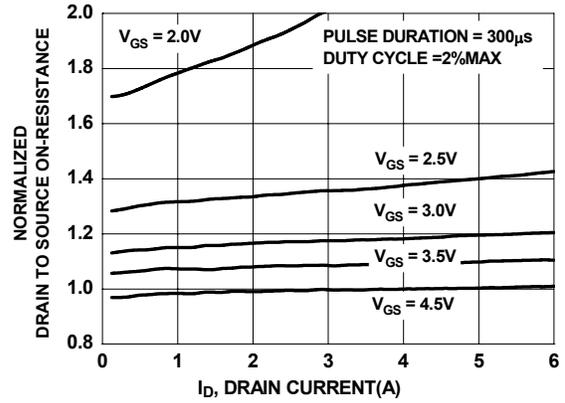


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

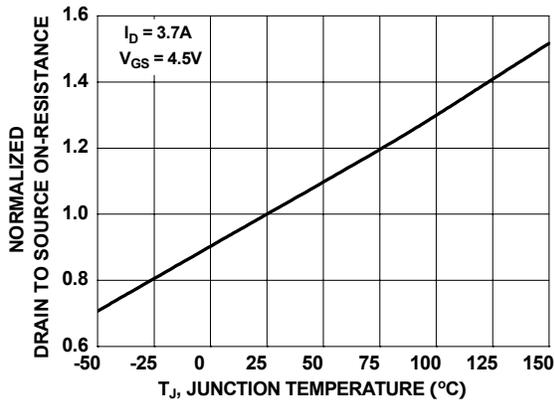


Figure 3. Normalized On-Resistance vs Junction Temperature

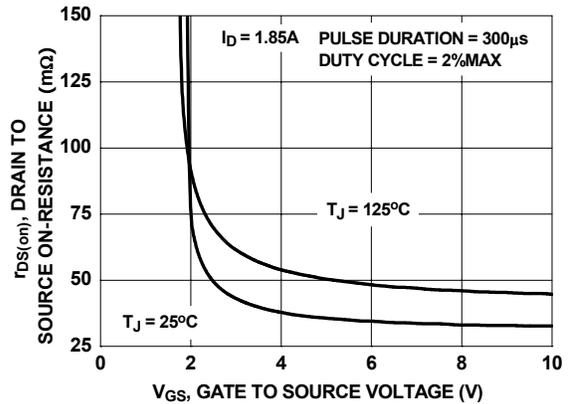


Figure 4. On-Resistance vs Gate to Source Voltage

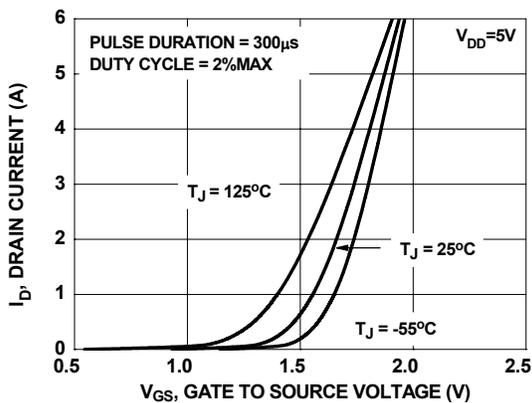


Figure 5. Transfer Characteristics

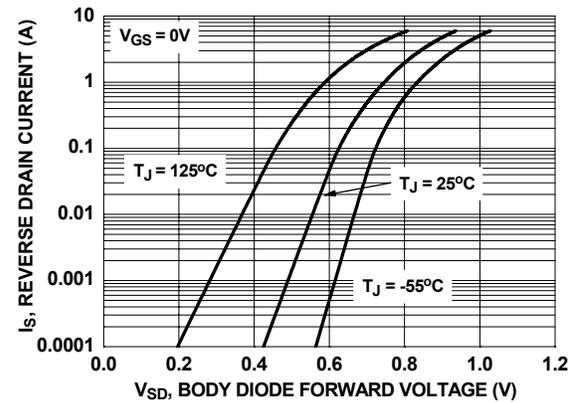


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

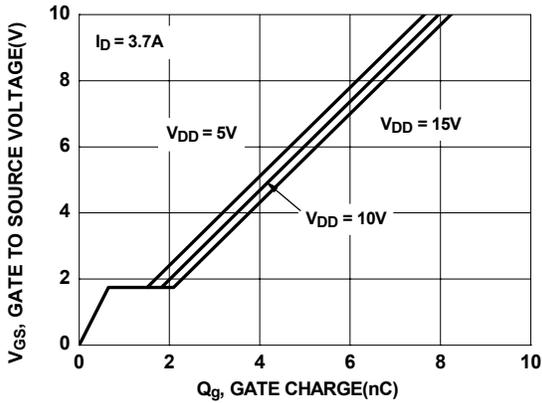


Figure 7. Gate Charge Characteristics

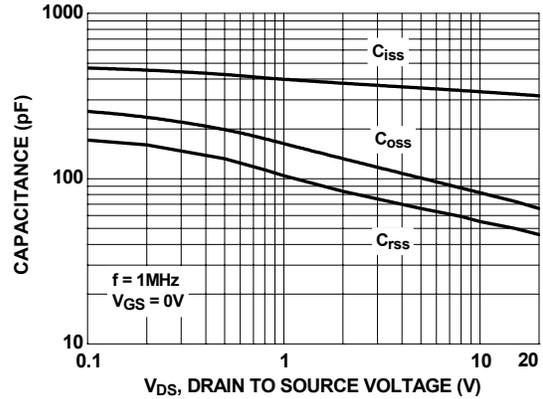


Figure 8. Capacitance Characteristics

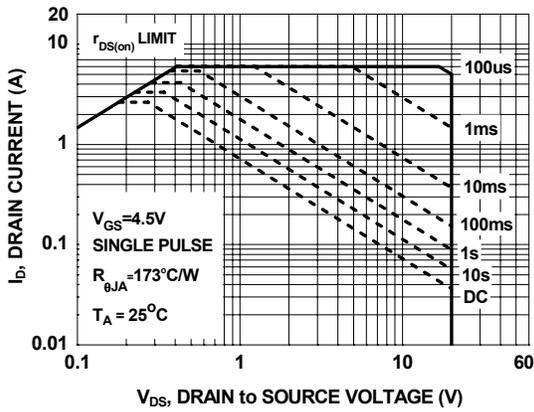


Figure 9. Forward Bias Safe Operating Area

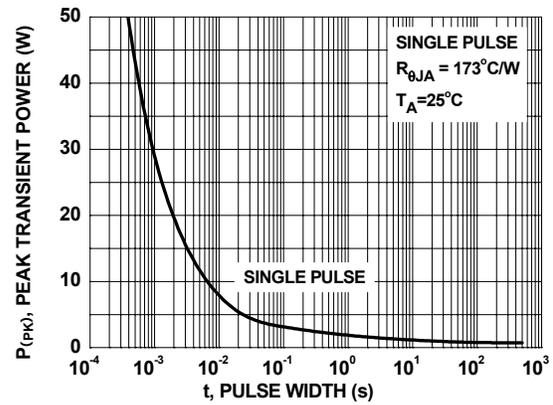


Figure 10. Single Pulse Maximum Power Dissipation

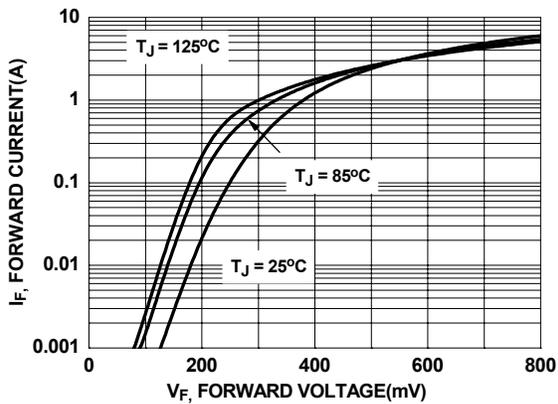


Figure 11. Schottky Diode Forward Current

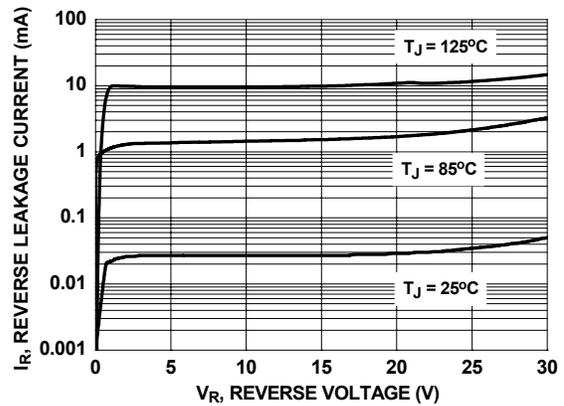
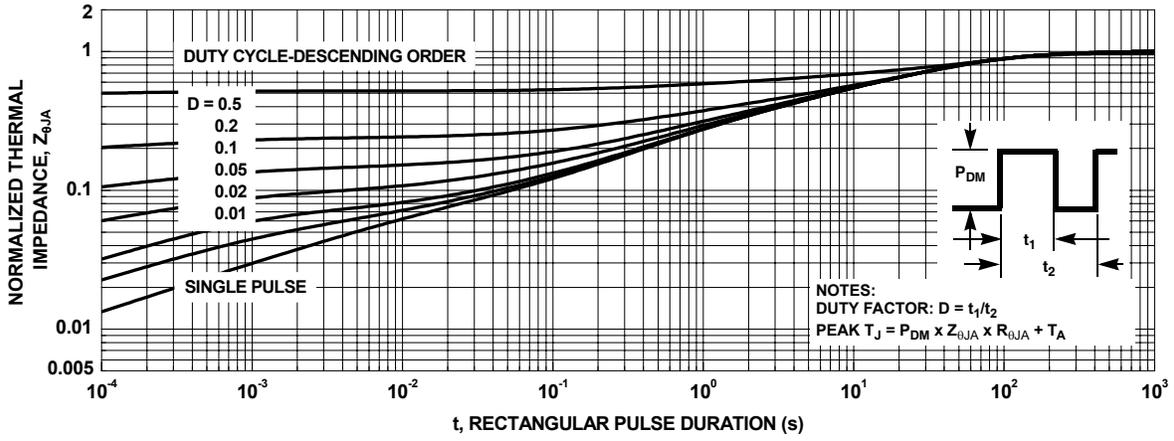
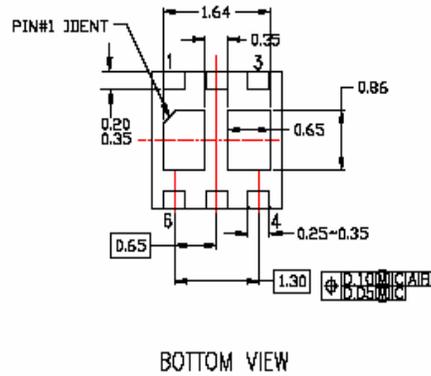
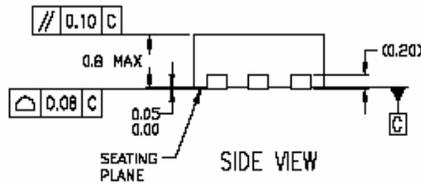
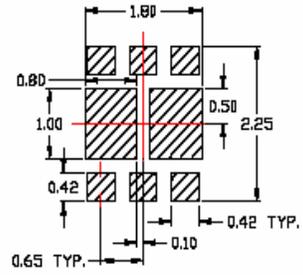
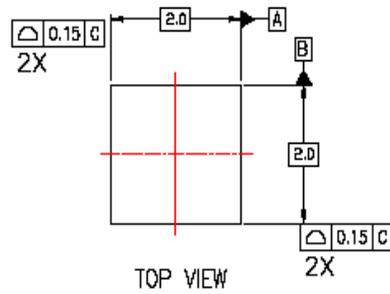


Figure 12. Schottky Diode Reverse Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted





NOTES:

- A. CONFORMS TO JEDEC REGISTRATION MO-229, VARIATION VCCC, DATED 11/2001
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994

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